



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

HIRASE, Masaki et al.

Serial No.: **09/908,941**

Filed: **July 20, 2001**

Group Art Unit **2812**

Examiner: **Jennifer M. Kennedy**

P.T.O. Confirmation No.: 1043

For. **SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME**

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: August 29, 2002

Sir:

In response to the Office Action dated June 13, 2002, please amend the above-identified application as set forth below:

IN THE CLAIMS:

Please amend claims 3 and 7 as follows:

SUB B1 3. (Amended) A method for manufacturing a semiconductor device, the method comprising:

a' forming an element partitioning trench and a mask aligning trench in a semiconductor substrate;

depositing an insulation in the element partitioning trench and the mask aligning trench by performing high density plasma chemical vapor deposition;

applying a protective mask on the insulation deposited in the element

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